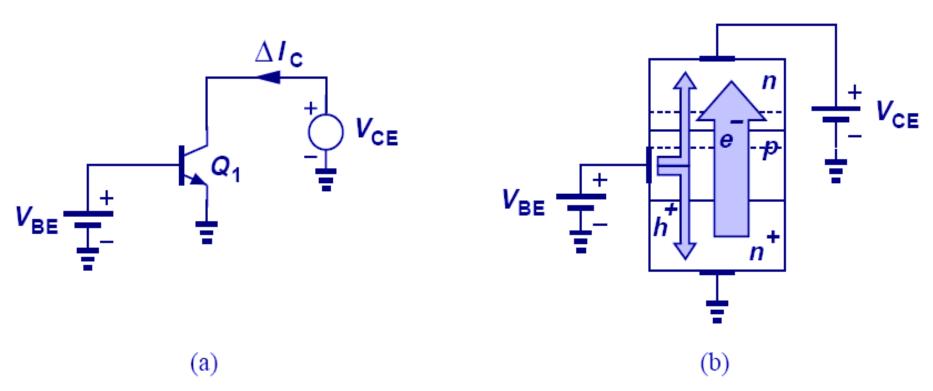
Lecture 5

<u>OUTLINE</u>

- Bipolar Junction Transistor (BJT) (Cont'd)
 - BJT operation in saturation mode
 - PNP BJT
 - Examples of small signal models

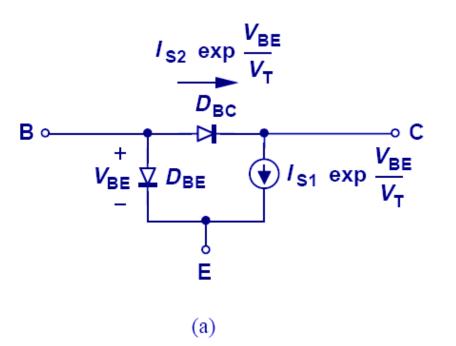
Reading: Chapter 4.5-4.6

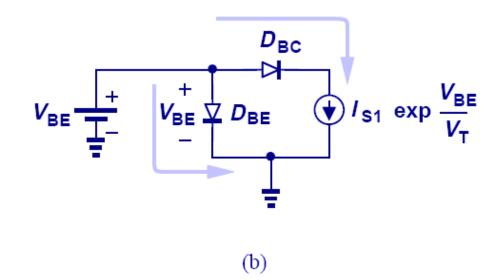
Bipolar Transistor in Saturation



 When collector voltage drops below base voltage and forward biases the collector-base junction, base current increases and the current gain factor, β,

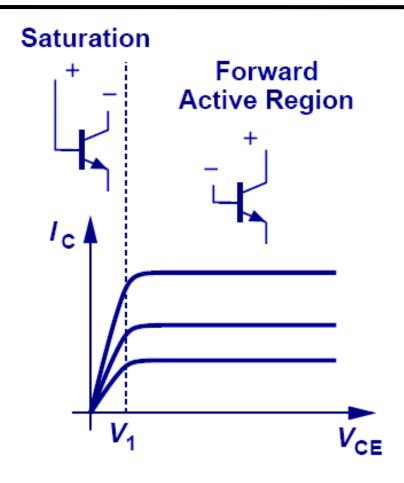
Large-Signal Model for Saturation Region





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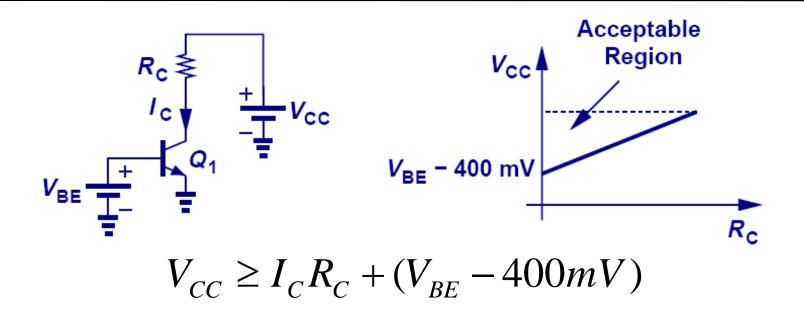
Overall I/V Characteristics



• The speed of the BJT also drops in saturation.

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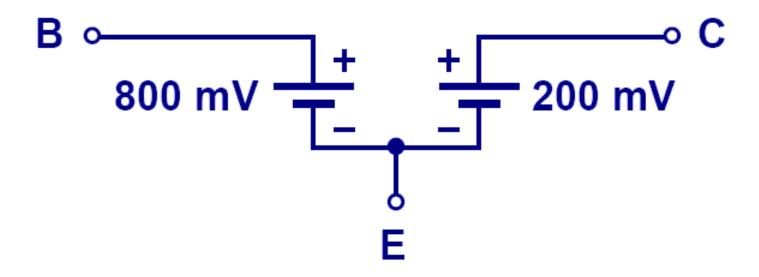
Example: Acceptable VCC Region



- In order to keep BJT at least in soft saturation region, the collector voltage must not fall below the base voltage by more than 400mV.
- A linear relationship can be derived for V_{CC} and R_C and an acceptable region can be chosen.

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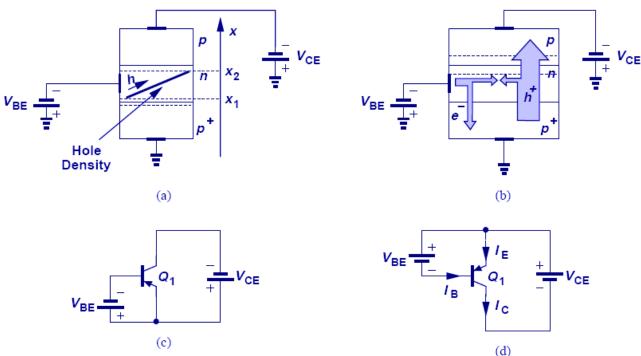
Deep Saturation



 In deep saturation region, the transistor loses its voltage-controlled current capability and V_{CE} becomes constant.

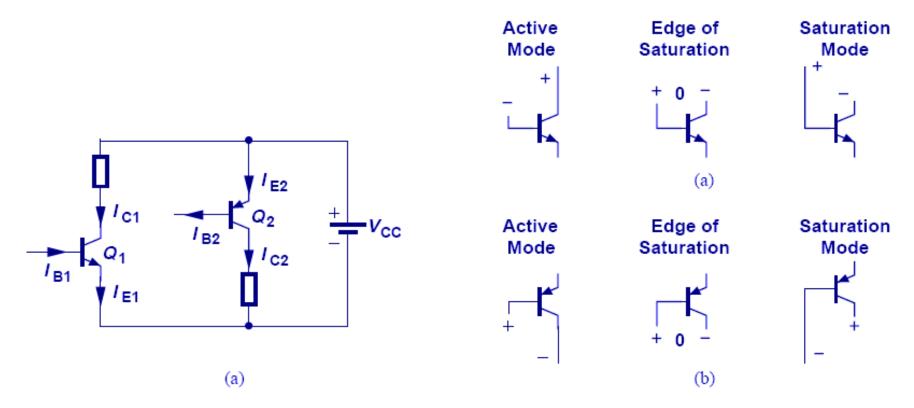
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PNP Transistor



- With the polarities of emitter, collector, and base reversed, a PNP transistor is formed.
- All the principles that applied to NPN's also apply to PNP's, with the exception that emitter is at a higher potential than base and base at a higher potential than collector.

A Comparison between NPN and PNP Transistors



 The figure above summarizes the direction of current flow and operation regions for both the NPN and PNP BJT's.

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PNP Equations with Early Effect

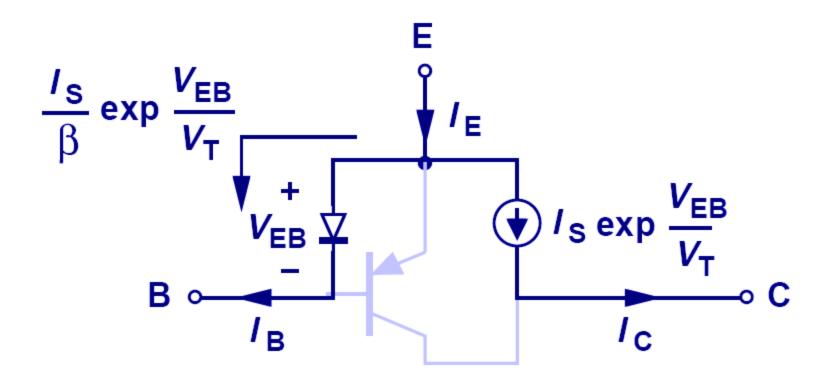
$$I_{C} = I_{S} \exp \frac{V_{EB}}{V_{T}}$$

$$I_{B} = \frac{I_{S}}{\beta} \exp \frac{V_{EB}}{V_{T}}$$

$$I_{E} = \frac{\beta + 1}{\beta} I_{S} \exp \frac{V_{EB}}{V_{T}}$$

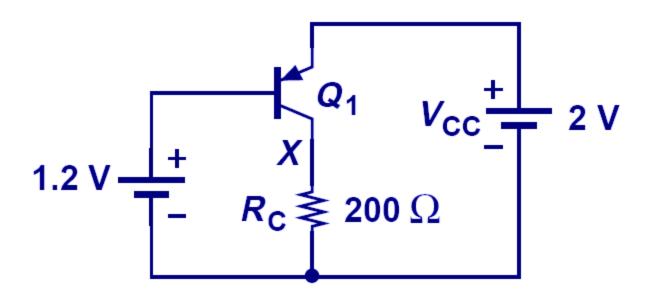
$$I_{C} = \left(I_{S} \exp \frac{V_{EB}}{V_{T}}\right) \left(1 + \frac{V_{EC}}{V_{A}}\right)$$

Large Signal Model for PNP



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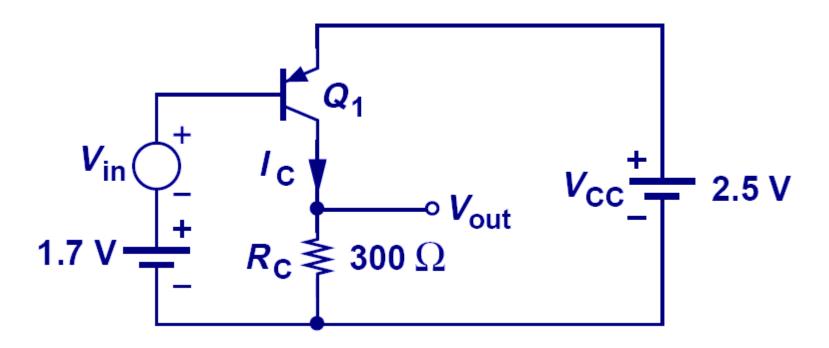
PNP Biasing



 Note that the emitter is at a higher potential than both the base and collector.

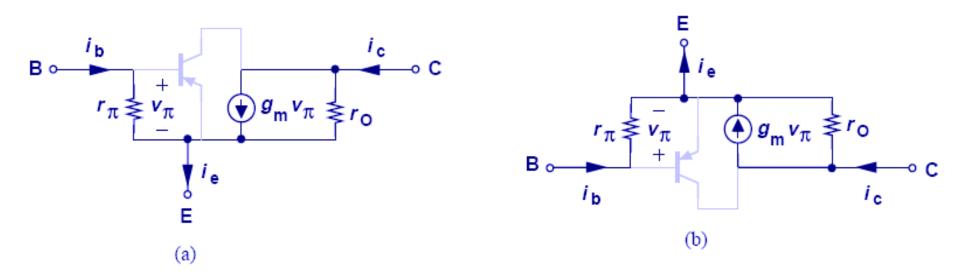
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Small Signal Analysis



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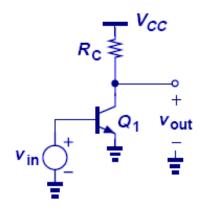
Small-Signal Model for PNP Transistor

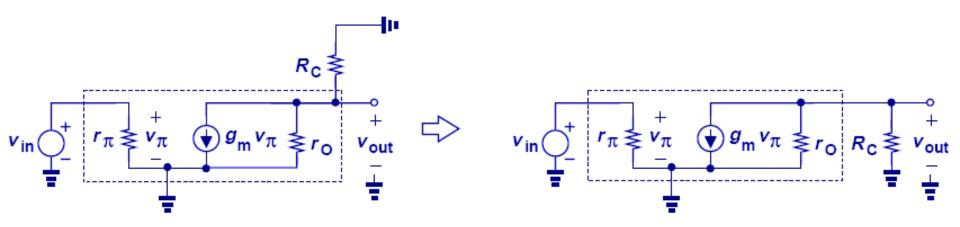


 The small signal model for PNP transistor is exactly IDENTICAL to that of NPN. This is not a mistake because the current direction is taken care of by the polarity of VBE.

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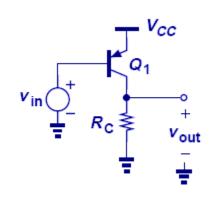
Small Signal Model Example I

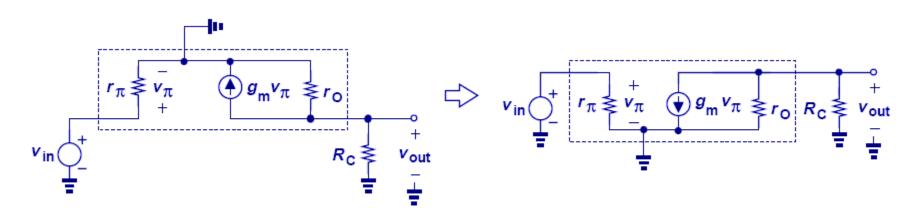




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Small Signal Model Example II

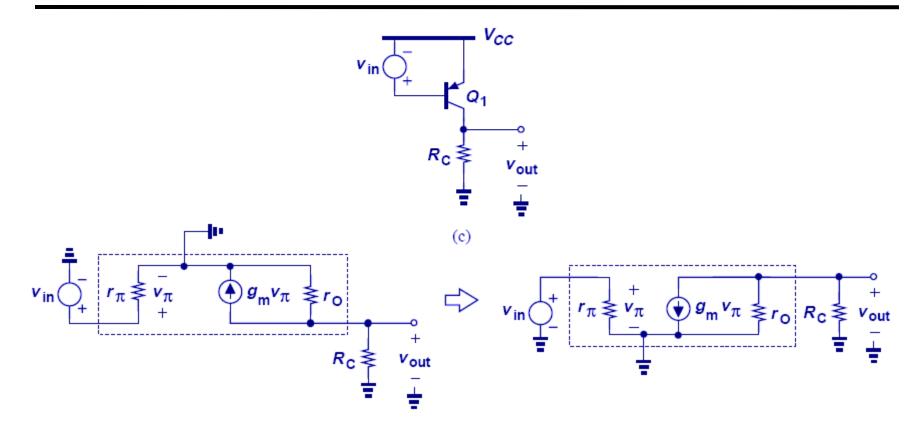




Small-signal model is identical to the previous ones.

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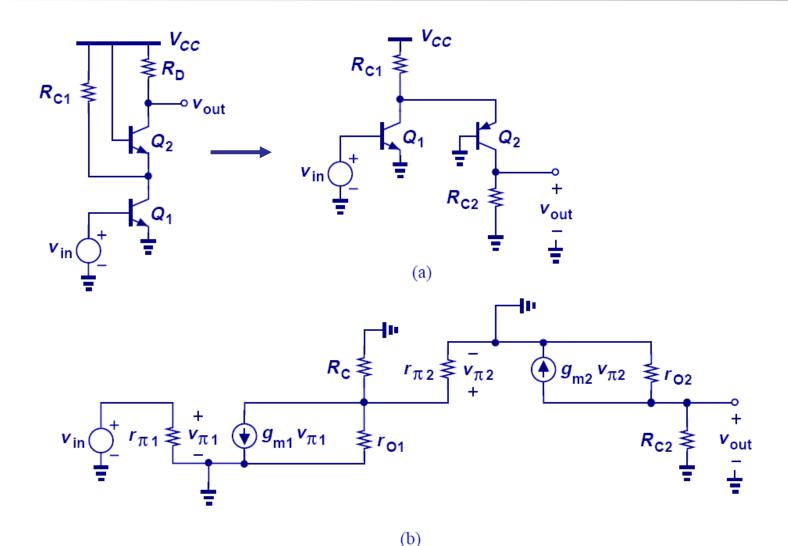
Small Signal Model Example III



• Since during small-signal analysis, a constant voltage supply is considered to be AC ground, the final small-signal model is identical to the previous two.

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Small Signal Model Example IV



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